

Contents

1	Device basics	1
1.1	Introduction	1
1.2	SCR current–voltage characteristics	3
1.3	Basic SCR construction features	7
1.4	Gate triggering	8
1.5	Holding current	11
1.6	Triggering a shorted emitter SCR	12
2	Current Gain	15
2.1	Variation of current gain with current	15
2.2	Current gain measurement	20
3	Thyristor Maximum Voltage Blocking Capability	24
3.1	Introduction	24
3.2	Maximum forward-blocking capability V_{BO}	26
3.3	Maximum reverse-blocking capability	30
3.4	The punch-through condition	33
3.5	Temperature dependence	33
3.6	Surface breakdown	35
3.7	Reverse-conducting thyristor	35
4	Some High-Injection-Level Effects	39
4.1	Introduction	39
4.2	Ambipolar mobility and diffusivity	40

4.3	Mobility and diffusivity versus current density	40
4.4	Lifetime at high injection levels	42
4.5	High-low junctions at high current densities	44
4.6	Current gain fall-off	44
5	The Gate-Triggered SCR Turn-On Transient	46
5.1	Introduction	46
5.2	Charge-control model of a bipolar transistor	48
5.3	Charge-control model of a p-n-p-n structure	50
5.4	Delay time	52
5.5	Rise time with a resistive load	54
5.6	Rise time with inductive load	56
5.7	Propagation of the on state	57
6	The Nongated, Undesirable Thyristor Triggering	62
6.1	Introduction	62
6.2	Thermal turn on	62
6.3	Light triggering	64
6.4	Voltage triggering	65
7	Thyristor Voltage Drop in the On State	73
7.1	Introduction	73
7.2	Herlet's closed-form p-i-n diode analysis	75
7.3	Kokosa's numerical analysis	75
7.4	Numerical analysis of Cornu and Lietz	76
7.5	Otsuka's forward-drop analysis	77
8	SCR Turn-off Transient	88
8.1	Introduction	88
8.2	Storage time t_{s_1}	90
8.3	Fall time t_{f_1}	91
8.4	Storage time t_{s_2}	93
8.5	Fall time t_{f_2}	94
8.6	Effect of the gate current	94
8.7	Simplified approaches	95
8.8	Experimental data	96
9	Gate Turn-off Thyristor (GTO)	98
9.1	Introduction	98
9.2	Plasma-pinching mechanism	100
9.3	Turn-off velocity	102
9.4	Pinching (focusing) time and turn-off gain	103
9.5	Maximum anode and gate currents	104

9.6	Plasma-pinching in the ungated n base	105
9.7	Theoretical model compared with experiment	106
10	Thyristor di/dt and Current Pulse Capability	109
10.1	Introduction	109
10.2	Test circuit for gate-triggered di/dt	111
10.3	Initial turn-on region	111
10.4	di/dt capability of the gated and nongated turn on	113
10.5	Localized temperature rise for a short single pulse	115
10.5	Temperature rise for long or recurrent pulses	116
10.7	Temperature rise and transient thermal impedance during turn-on spreading	117
10.8	Methods of increasing the initial turn-on area	119
10.9	Emitter gate	124
10.10	Emitter shorts versus the turn-on time	126
10.11	Beam-fired thyristor	126
10.12	Field-controlled thyristor	128
11	Bidirectional p-n-p-n Switches	131
11.1	Introduction	131
11.2	Bidirectional p-n-p-n diode switch	133
11.3	Current distribution across a forward-biased junction bounded by resistive layers (current-crowding effect)	135
11.4	Junction gate	140
11.5	Remote gate	143
11.6	Triac	145
12	Commutation of Triacs	154
12.1	Introduction	154
12.2	Current and voltage waveforms during commutation	155
12.3	Role of stored charges in triac commutation	159
12.4	Recovery of a $p^+ - n$ abrupt-junction diode	161
12.5	Snubber networks for dv/dt suppression	170
13	Silicon Surface	173
13.1	Introduction	173
13.2	Ideal MOS diode	174
13.3	Silicon surface states and charges	182

14	Avalanche Breakdown Enhancement by Mesa Contouring	197
14.1	Introduction	198
14.2	Positive and negative bevel angles	199
14.3	Theoretical approach to the field computation in the depletion region	199
14.4	Negative bevel angle	202
14.5	Positively beveled junctions	209
14.6	Novel approaches to beveling	211
15	Planar-Junction Avalanche Breakdown Improvement	216
15.1	Introduction	216
15.2	Diffused guard ring	219
15.3	Junction field plate, annular ring, and channel stopper	220
15.4	Resistive field plate	227
15.5	p-n junction with field limiting rings	231
15.6	Etch-contoured planar junctions	239
16	Thyristor Thermal Response	242
16.1	Introduction	242
16.2	Heat generation and absorption in the forward-biased thyristor	243
16.3	Determination of junction temperature	248
16.4	Generalized concept of thermal impedance	255
16.5	Device temperature response to an arbitrary power waveshape	260
16.6	Thyristor thermal impedance measurement	265
16.7	Computer-aided thermal analysis	266
17	Thyristor Circuits Basics	269
17.1	Introduction	269
17.2	SCR and triac control and triggering methods	271
17.3	Thyristor triggering devices	280
17.4	Commutation	288
17.5	Effect of an impedance between the gate and cathode of a thyristor	291
17.6	Thyristor protection circuits	292
17.7	Some thyristor applications	294